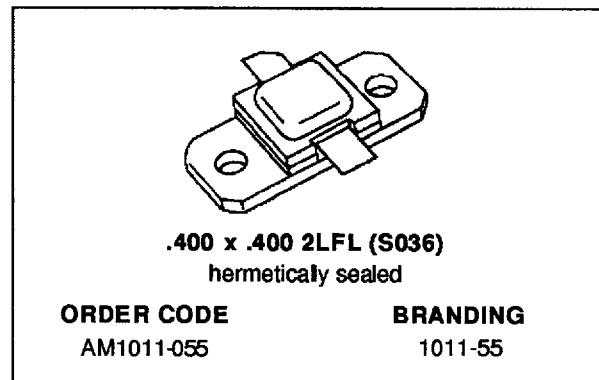


## RF & MICROWAVE TRANSISTORS L-BAND AVIONICS APPLICATIONS

PRELIMINARY DATA

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- 10:1 VSWR CAPABILITY
- LOW THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 55\text{ W}$  MIN. WITH 9.2 dB GAIN

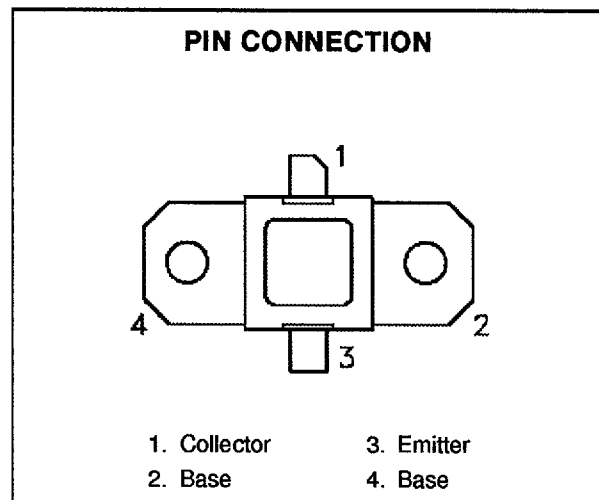


### DESCRIPTION

The AM1011-055 device is a high power Class C transistor specifically designed for L-Band Avionics transponder/interrogator output and driver applications.

This device is capable of operation over a wide range of pulse widths, duty cycles, and temperatures and is capable of withstanding 10:1 output VSWR at rated RF conditions. Low RF thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The AM1011-055 is supplied in the AMPAC™ Hermetic Metal/Ceramic package with internal Input/Output matching structures.



### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$P_{DISS}$	Power Dissipation* ( $T_C \leq 100^{\circ}\text{C}$ )	91	W
$I_C$	Device Current*	3.79	A
$V_{CC}$	Collector-Supply Voltage*	50	V
$T_J$	Junction Temperature (Pulsed RF Operation)	250	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	- 65 to +200	$^{\circ}\text{C}$

### THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	1.1	$^{\circ}\text{C}/\text{W}$
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\*Applies only to rated RF amplifier operation

# AM1011-055

## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV <sub>CBO</sub>	I <sub>C</sub> = 7.5mA	I <sub>E</sub> = 0mA	65	—	—	V
BV <sub>EBO</sub>	I <sub>E</sub> = 3mA	I <sub>C</sub> = 0mA	3.5	—	—	V
BV <sub>CER</sub>	I <sub>C</sub> = 7.5mA	R <sub>BE</sub> = 10Ω	65	—	—	V
I <sub>CES</sub>	V <sub>CE</sub> = 50V		—	—	4	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 1A	5	—	200	—

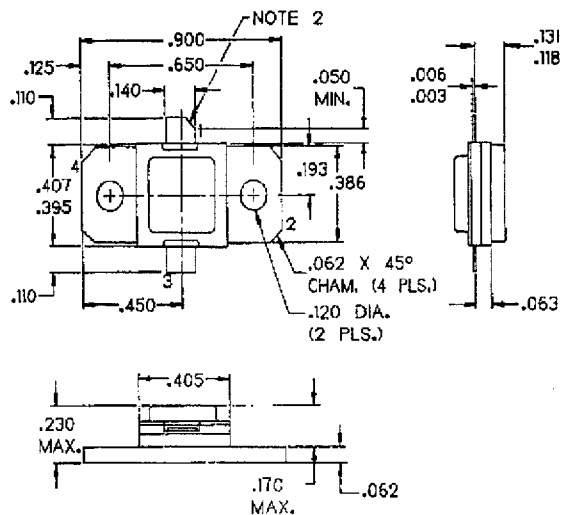
### DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P <sub>OUT</sub>	f = 1090MHz	P <sub>IN</sub> = 6.6W	V <sub>CC</sub> = 50V	55	—	—	W
η <sub>c</sub>	f = 1090MHz	P <sub>IN</sub> = 6.6W	V <sub>CC</sub> = 50V	48	—	—	%
G <sub>p</sub>	f = 1090MHz	P <sub>IN</sub> = 6.6W	V <sub>CC</sub> = 50V	9.2	—	—	dB

Note: Pulse Width = 32 μs  
Duty Cycle = 2%

### PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J133102E



#### NOTES:

1. ALL TOLERANCE ± .010 EXCEPT WHERE NOTED; DIMENSIONS IN INCHES.
2. COLLECTOR LEAD CHAMFER 45° NOM. X .040 NOM.